

Product Overview

BDV65B: 10 A, 100 V NPN Darlington Bipolar Power Transistor

For complete documentation, see the data sheet.

The 10 A, 100 V NPN Bipolar Power Transistor is for use as an output devices in complementary general purpose amplifier applications. The BDV65B (NPN) and BDV64B (PNP) are complementary devices.

Features

- High DC Current Gain $H_{FE} = 1000$ (min.) @ 5 Adc
- Monolithic Construction with Built-in Base Emitter Shunt Resistors
- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	$V_{CE(sat)}$ Max (V)	h_{FE} Min (k)	h_{FE} Max (k)	f_T Min (MHz)	Package Type
BDV65BG	Pb-free	Active	NPN	10	100	2	1	-	-	TO-247

For more information please contact your local sales support at www.onsemi.com.

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